Dow

**PATENT** 

CASE NAME/No.: SP02-152

## ETHNOTHE UNITED STATES PATENT AND TRADEMARK OFFICE

Inventor:

Guillermo Guzman et al.

Serial No:

Filing Date:

10/668873

0.100.100.00

Title:

9/23/2003

UNDER LAYER FOR POLYSILICON TFT

Art Group Unit: 2826

Examiner: Thomas L. Dickey

RESPONSE

Commissioner for Patents Alexandria, VA 22313-1450

## RESPONSE TO EXAMINER'S RESTRICTION REQUIREMENT

In the Office Action dated June 16, 2004, designated as Paper No. 200406 in the above-captioned application, the Examiner issued a Restriction Requirement identifying the following groups of claims as being drawn to potentially distinct inventions:

Group I. Claims 15 - 18, drawn to a method, classified in class 438, subclass 958; and Group II. Claims 1 - 14 and 19, drawn to a device, classified in class 257, subclass 636.

A provisional election to Group II, claims 1-14 and 19 is made without traverse.

As a formality, Applicants hereby cancel claims 15-18, without prejudice.

## IN THE CLAIMS

1. (Original) A semiconductor device comprising:

a substrate suitable for use in electronic and integrated circuits;

- a layer of refractory polycrystalline material formed on at least a portion of the substrate; and
- a layer of polycrystalline silicon formed on the refractory layer.
- 2. (Original) A semiconductor device according to claim 1 wherein said device is a thin film transistor (TFT) suitable for applications selected from the group consisting of liquid crystal displays (LCDs) and light emitting diodes (LEDs).
- 3. (Original) A semiconductor device according to claim 1 wherein the substrate is glass, glass-ceramic, ceramic, metal or plastic.